

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

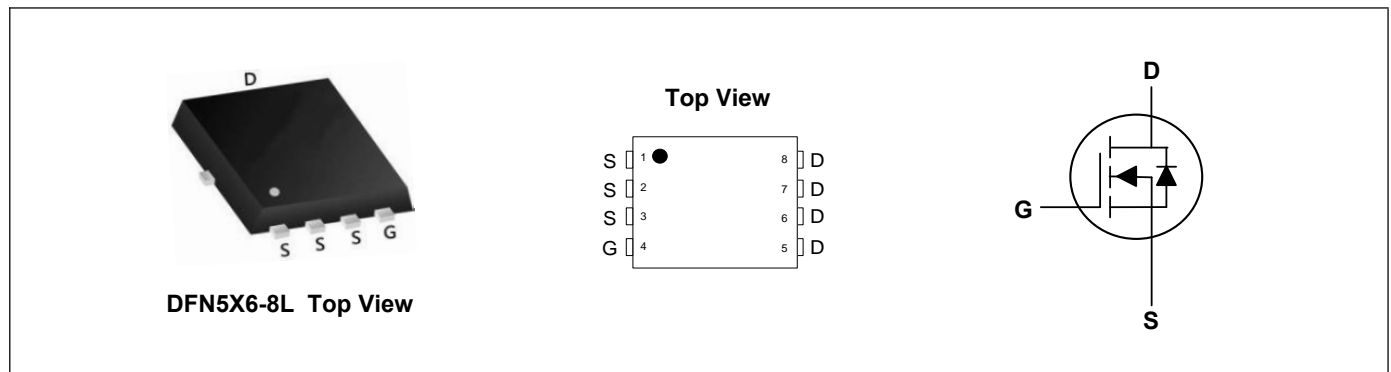
### Product Summary



$V_{DS}$	80	V
$I_D$	122	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	6.5	m $\Omega$

### Applications

- High Frequency Point-of-Load, Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- LCD/LED Back light



### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	80	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_C=25^\circ\text{C}$	122	A
Continuous Drain Current, $V_{GS} @ 10V^1$	$I_D @ T_C=100^\circ\text{C}$	78.6	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	300	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	246.4	mJ
Avalanche Current	$I_{AS}$	70.2	A
Total Power Dissipation <sup>4</sup>	$P_D @ T_C=25^\circ\text{C}$	156	W
Storage Temperature Range	$T_{STG}$	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	---	62	$^\circ\text{C/W}$
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	0.8	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	80	---	---	V
BV <sub>DSS</sub> Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Reference to 25°C, I <sub>D</sub> =1mA	---	-0.059	---	V/°C
Static Drain-Source On-Resistance <sup>2</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	---	6.5	mΩ
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	2	---	4	V
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub>		---	-4.6	---	mV/°C
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =64V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =64V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =30A	---	50	---	S
Gate Resistance	R <sub>g</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.4	---	Ω
Total Gate Charge (10V)	Q <sub>g</sub>	V <sub>DS</sub> =64V, V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	83.7	---	nC
Gate-Source Charge	Q <sub>gs</sub>		---	28.6	---	
Gate-Drain Charge	Q <sub>gd</sub>		---	29.3	---	
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =40V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =30A	---	38.1	---	ns
Rise Time	T <sub>r</sub>		---	73.3	---	
Turn-Off Delay Time	T <sub>d(off)</sub>		---	51.6	---	
Fall Time	T <sub>f</sub>		---	26.1	---	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	5580	---	pF
Output Capacitance	C <sub>oss</sub>		---	571	---	
Reverse Transfer Capacitance	C <sub>rss</sub>		---	278	---	

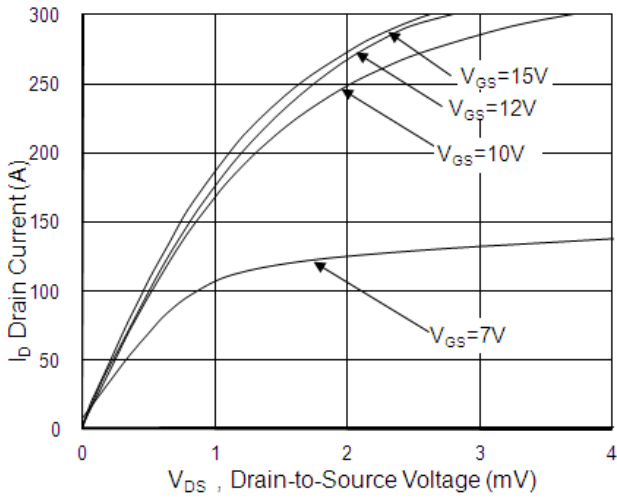
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current <sup>1,5</sup>	I <sub>S</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	122	A
Pulsed Source Current <sup>2,5</sup>	I <sub>SM</sub>		---	---	300	A
Diode Forward Voltage <sup>2</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =30A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	26.7	---	nS
Reverse Recovery Charge	Q <sub>rr</sub>		---	27.9	---	nC

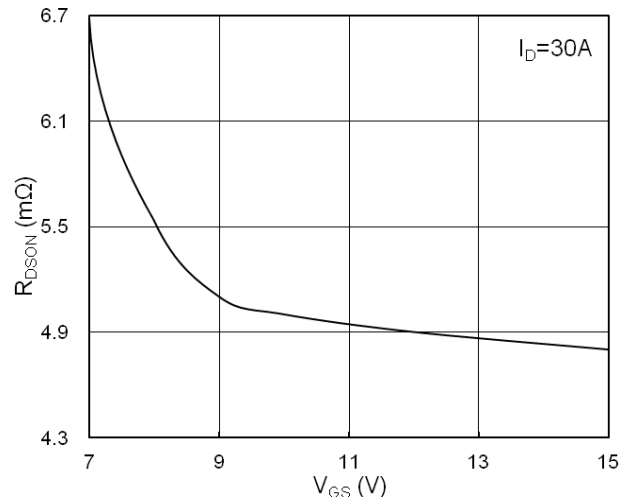
**Note:**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=70.2A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

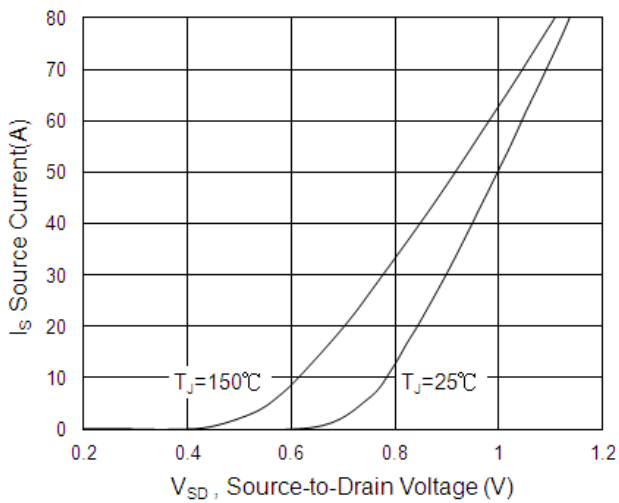
**Typical Characteristics**



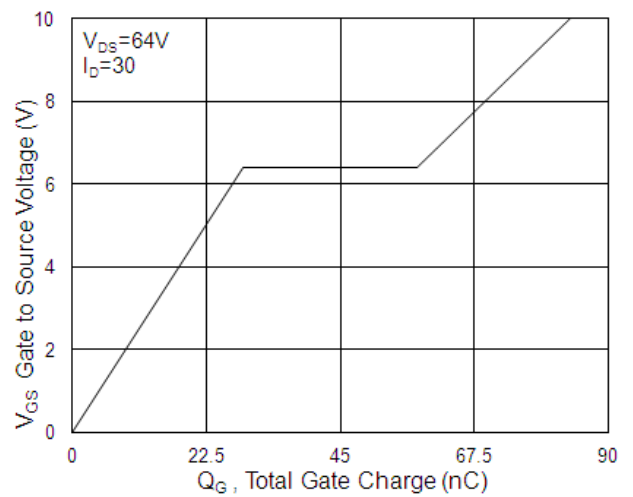
**Fig.1 Typical Output Characteristics**



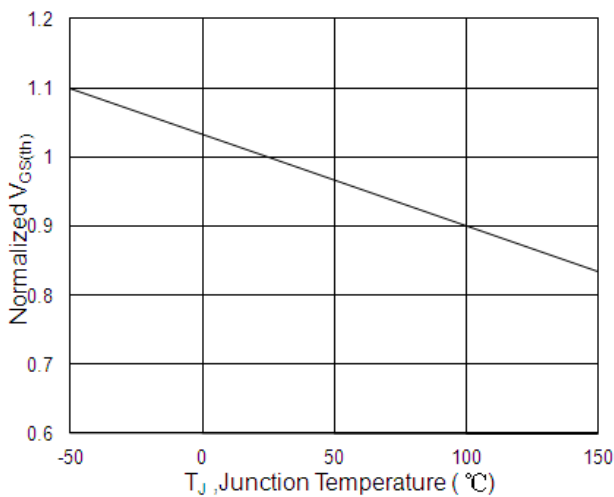
**Fig.2 On-Resistance v.s Gate-Source**



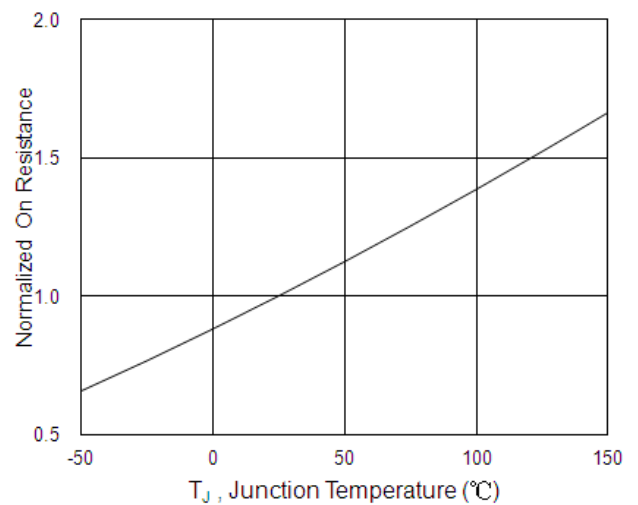
**Fig.3 Forward Characteristics of Reverse**



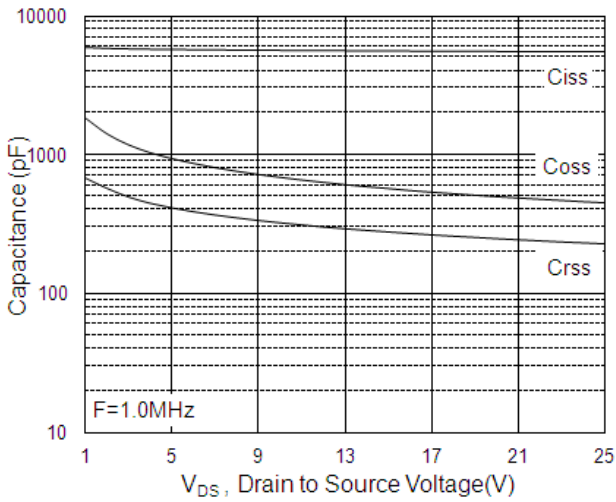
**Fig.4 Gate-Charge Characteristics**



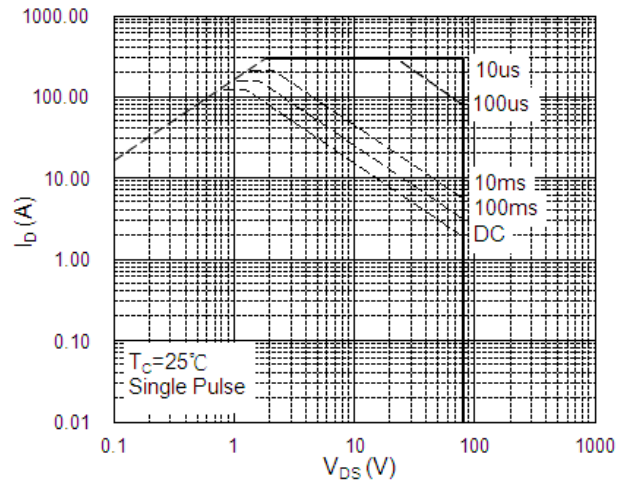
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



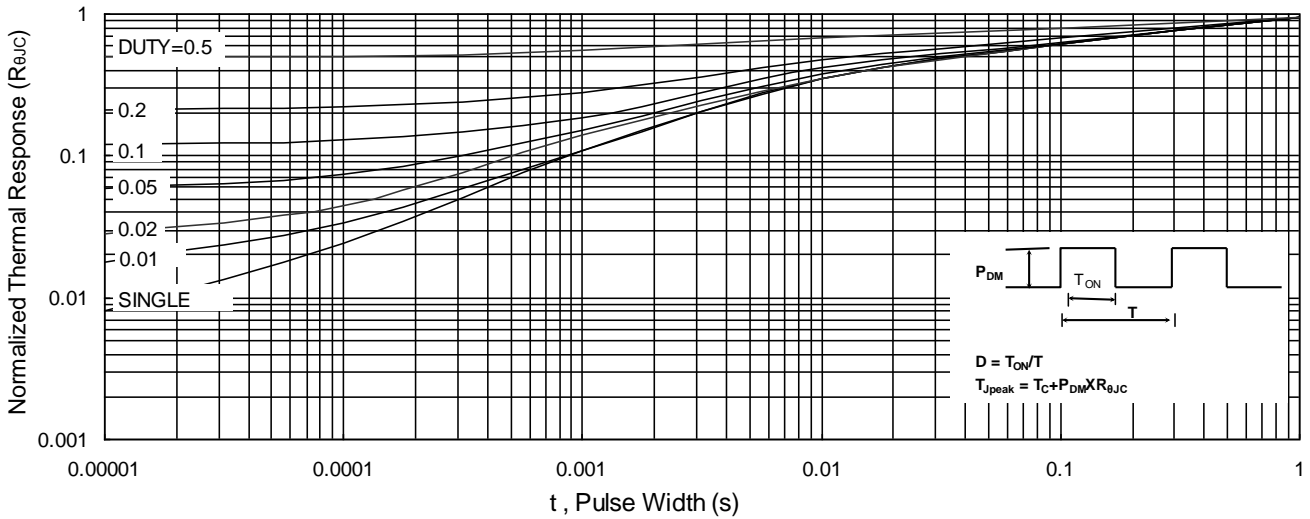
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



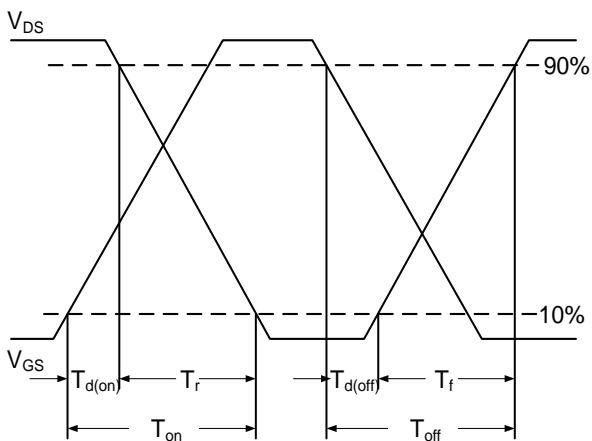
**Fig.7 Capacitance**



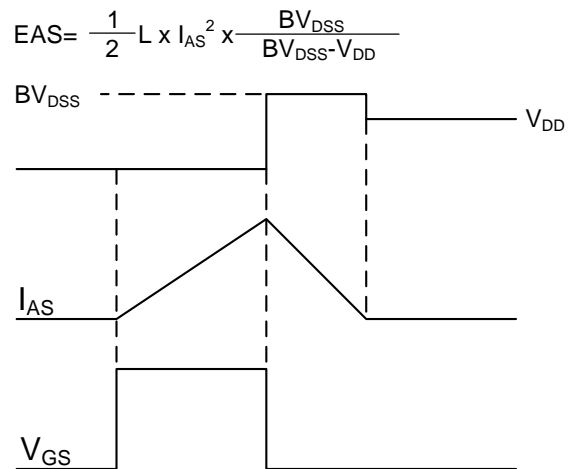
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

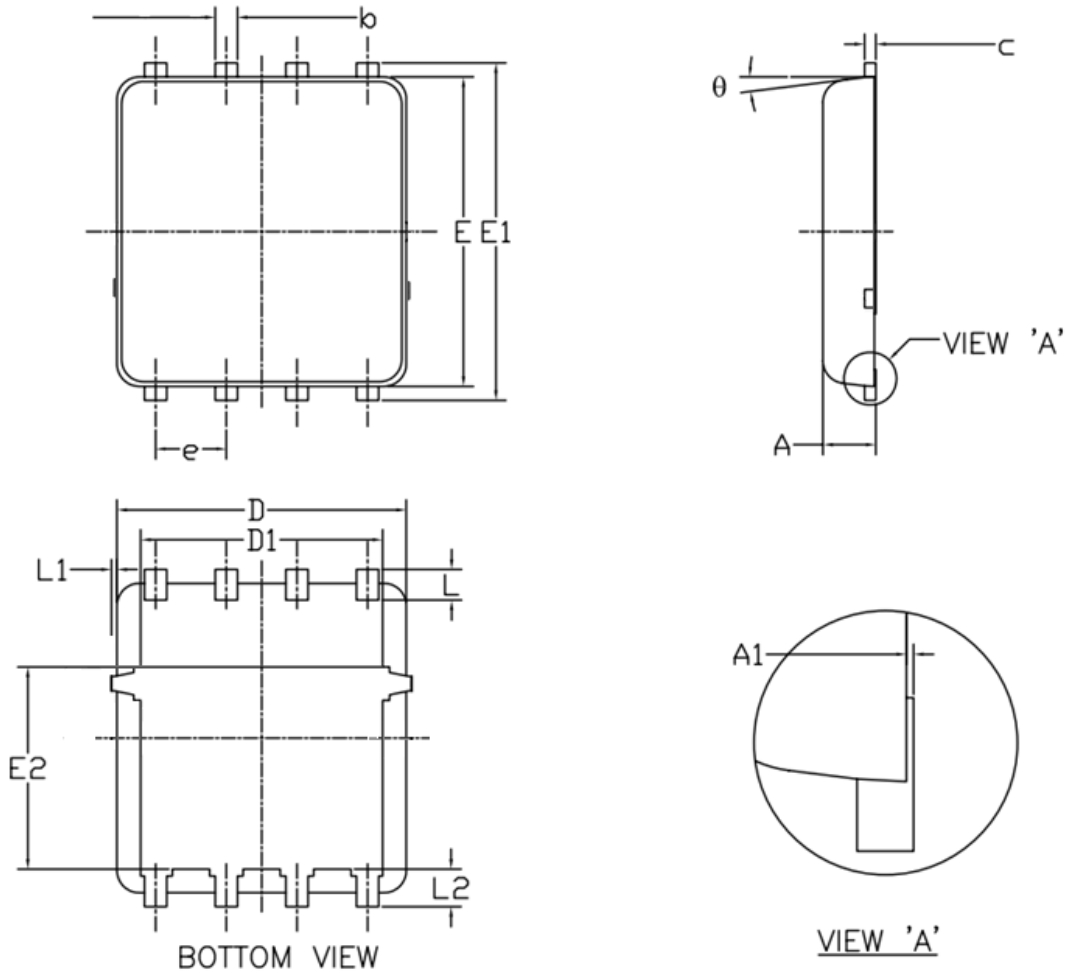


**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

**DFN5X6-8L Package Outline Dimensions**



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
<b>A</b>	0.90	1.00	1.20	<b>E1</b>	5.90	6.10	6.35
<b>A1</b>	0.00	--	0.05	<b>E2</b>	3.38	3.58	3.92
<b>b</b>	0.30	0.40	0.51	<b>e</b>	1.27 BSC		
<b>c</b>	0.20	0.25	0.33	<b>L</b>	0.51	0.61	0.71
<b>D</b>	4.80	4.90	5.40	<b>L1</b>	--	--	0.15
<b>D1</b>	3.61	4.00	4.25	<b>L2</b>	0.41	0.51	0.61
<b>E</b>	5.65	5.80	6.06	<b>θ</b>	0°	--	12°